

2SD1576

Silicon NPN Triple-Diffused Junction Mesa Type

Horizontal Deflection Output

■ Features

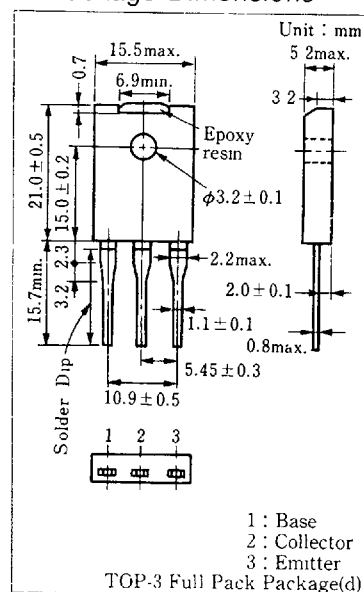
- High breakdown voltage and high reliability by glass passivation
- High speed switching
- Wide area of safety operation (ASO)
- "Full Pack" package for simplified mounting on a heat sink with one screw

■ Absolute Maximum Ratings (T_c=25°C)

Item	Symbol	Value	Unit
Collector-base voltage	V _{CB0}	1500	V
Collector-emitter voltage	V _{CE5}	1500	V
	V _{CE0}	700	V
Emitter-base voltage	V _{EB0}	6	V
Collector current	I _C	2	A
Peak collector current	I _{CP} *	6	A
Peak base current	I _{BP}	2.5	A
Reverse peak base current	I _{BP}	-1.5	A
Collector power dissipation	P _C	80	W
		2.5	
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 ~ +150	°C

* Non repetitive peak value

■ Package Dimensions



■ Electrical Characteristics (T_c=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I _{CBO}	V _{CB} = 750 V, I _E = 0			50	μA
		V _{CB} = 1500 V, I _E = 0			1	mA
Emitter-base voltage	V _{EB0}	I _E = 1 mA, I _C = 0	6			V
DC current gain	h _{FE}	V _{CE} = 5 V, I _C = 2 A	2		5	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 2 A, I _B = 1 A			5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 2 A, I _B = 1 A			1.5	V
Transition frequency	f _T	V _{CE} = 10 V, I _C = 0.5 A, f = 0.5 MHz		2		MHz
Fall time	t _f	I _C = 2.5 A, I _{Bend} = 1.1 A			1	μs
Storage time	t _{stg}	L _B = 10 μH			9	μs

